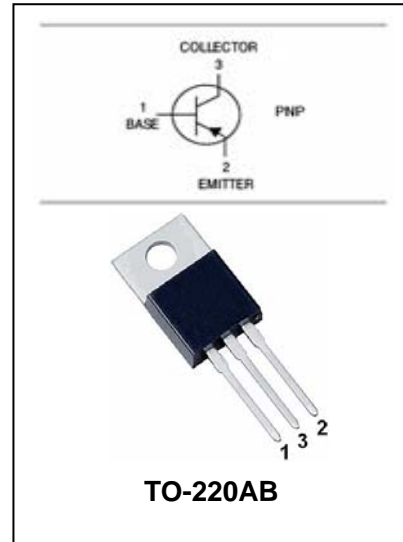


PNP Epitaxial Silicon Transistor

2SA1012

FEATURES

- Low Collector Saturation Voltage.
 $V_{CE(sat)} = -0.4V(\text{Max.})$ at $I_C = -3A$
- Complements the 2SC2562.
- High Speed Switching Time: $t_{stg} = 1.0\mu s(\text{Typ.})$



MAXIMUM RATING operating temperature range applies unless otherwise specified

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-5	A
P_C	Collector Dissipation	2	W
T_j, T_{stg}	Junction and Storage Temperature	-55 to +150	°C

PNP Epitaxial Silicon Transistor

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ELECTRICAL CHARACTERISTICS Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = -100\mu A, I_E = 0$	-60			V
Collector-emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-50			V
Emitter-base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector Cut-off Current	I_{CBO}	$V_{CB} = -50V, I_E = 0$			-1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = -5V, I_C = 0$			-1	μA
DC Current Gain	h_{FE}	$V_{CE} = -1V, I_C = -1A$ $V_{CE} = -1V, I_C = -3A$	70 30		240	
Collector-emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -3A, I_B = -0.15A$		-0.2	-0.4	V
Base-emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -3A, I_B = -0.15A$		-0.9	-1.2	V
Transition Frequency	f_T	$V_{CE} = -4V, I_C = -1A$		60		MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = -10V, I_E = 0,$ $f = 1MHz$		170		pF

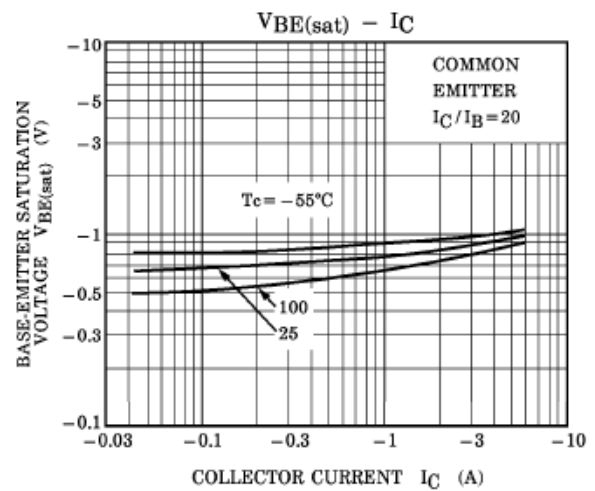
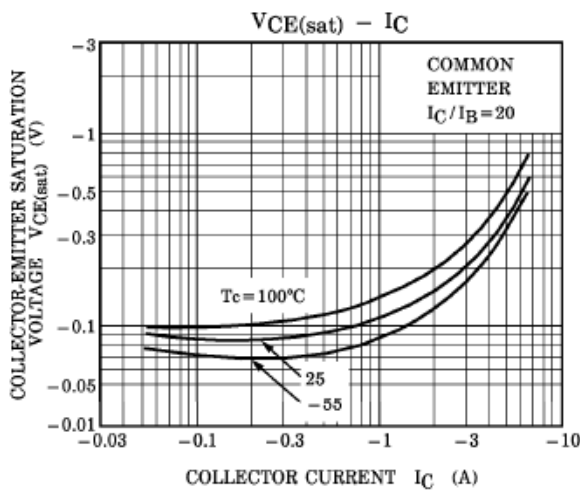
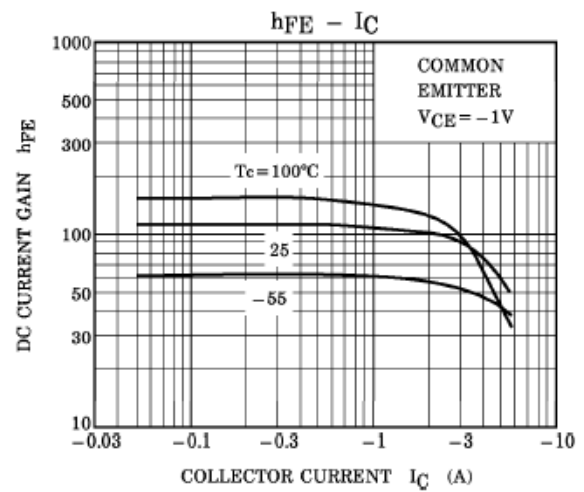
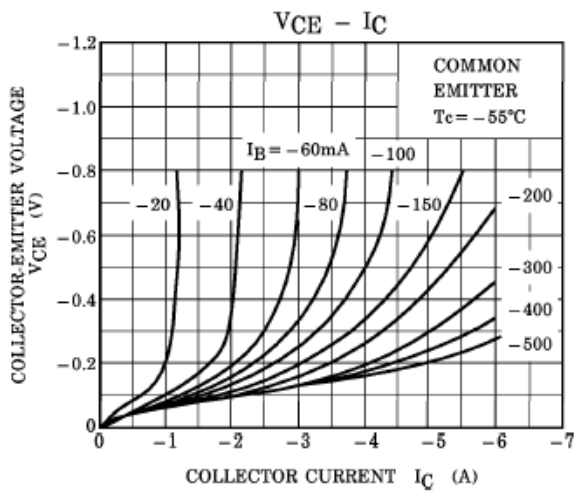
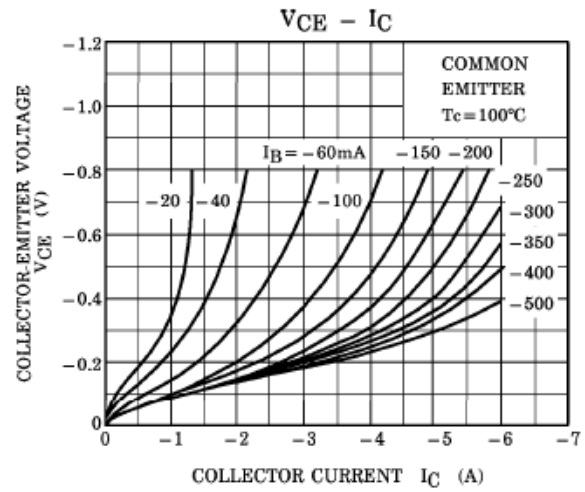
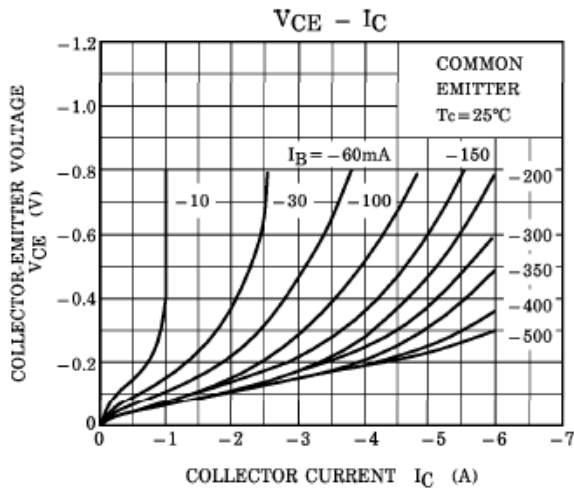
CLASSIFICATION OF h_{FE}

Range	O	Y
Marking	70-140	120-240

PNP Epitaxial Silicon Transistor

2SA1012

TYPICAL CHARACTERISTICS @ $T_a=25^\circ\text{C}$ unless otherwise specified



PNP Epitaxial Silicon Transistor

2SA1012

PACKAGE OUTLINE

Plastic surface mounted package

TO-220AB

